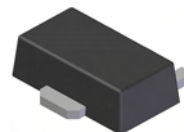


Features

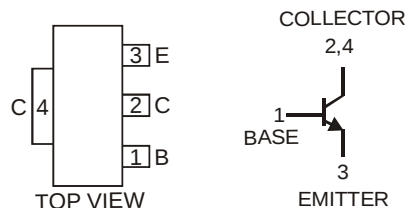
- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DXT2907A)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**



SOT89-3L

Mechanical Data

- Case: SOT89-3L
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish — Matte Tin annealed over Copper leadframe
(Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072 grams (approximate)



Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	75	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6	V
Peak Pulse Current	I _{CM}	800	mA
Continuous Collector Current	I _C	600	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	P _D	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @T _A = 25°C	R _{θJA}	125	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

1. No purposefully added lead.
2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
3. Device mounted on FR-4 PCB; pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Conditions
OFF CHARACTERISTICS (Note 4)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	75	—	V	I _C = 10μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	40	—	V	I _C = 10mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	6.0	—	V	I _E = 10μA, I _C = 0
Collector Cutoff Current	I _{CBO}	—	10	nA μA	V _{CB} = 60V, I _E = 0 V _{CB} = 60V, I _E = 0, T _A = 150°C
Collector Cutoff Current	I _{CEx}	—	10	nA	V _{CE} = 60V, V _{EB(OFF)} = 3.0V
Emitter Cutoff Current	I _{EBO}	—	10	nA	V _{EB} = 3.0V, I _C = 0
Base Cutoff Current	I _{BL}	—	20	nA	V _{CE} = 60V, V _{EB(OFF)} = 3.0V
ON CHARACTERISTICS (Note 4)					
DC Current Gain	h _{FE}	35	—	—	I _C = 100μA, V _{CE} = 10V
		50	—		I _C = 1.0mA, V _{CE} = 10V
		75	—		I _C = 10mA, V _{CE} = 10V
		100	300		I _C = 150mA, V _{CE} = 10V
		40	—		I _C = 500mA, V _{CE} = 10V
		35	—		I _C = 10mA, V _{CE} = 10V, T _A = -55°C
		50	—		I _C = 150mA, V _{CE} = 1.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	0.3 1.0	V	I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.6	1.2 2.0	V	I _C = 150mA, I _B = 15mA I _C = 500mA, I _B = 50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	8	pF	V _{CB} = 10V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{ibo}	—	25	pF	V _{EB} = 0.5V, f = 1.0MHz, I _C = 0
Current Gain-Bandwidth Product	f _T	300	—	MHz	V _{CE} = 20V, I _C = 20mA, f = 100MHz
Noise Figure	NF	—	4.0	dB	V _{CE} = 10V, I _C = 150μA, R _S = 1.0kΩ, f = 1.0kHz
SWITCHING CHARACTERISTICS					
Delay Time	t _d	—	10	ns	V _{CC} = 30V, I _C = 150mA,
Rise Time	t _r	—	25	ns	V _{EB(off)} = 0.5V, I _{B1} = 15mA
Storage Time	t _s	—	225	ns	V _{CC} = 30V, I _C = 150mA,
Fall Time	t _f	—	60	ns	I _{B1} = I _{B2} = 15mA

Notes: 4. Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.

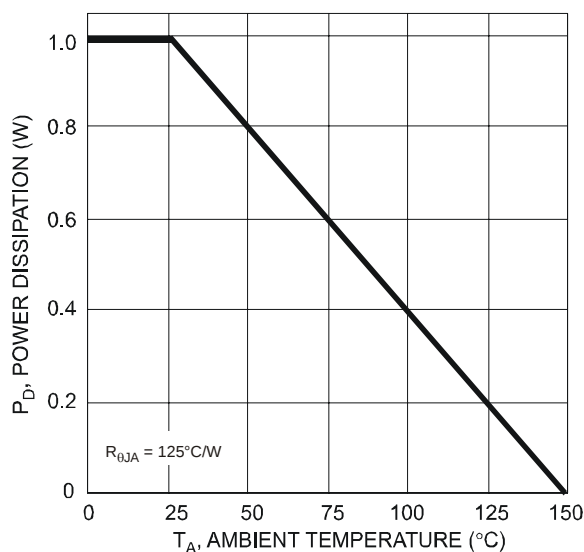


Fig. 1 Power Dissipation vs. Ambient Temperature

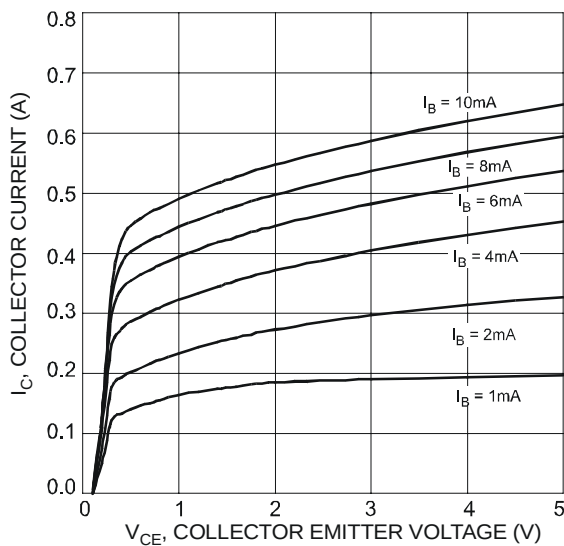


Fig. 2 Typical Collector Current vs. Collector Emitter Voltage

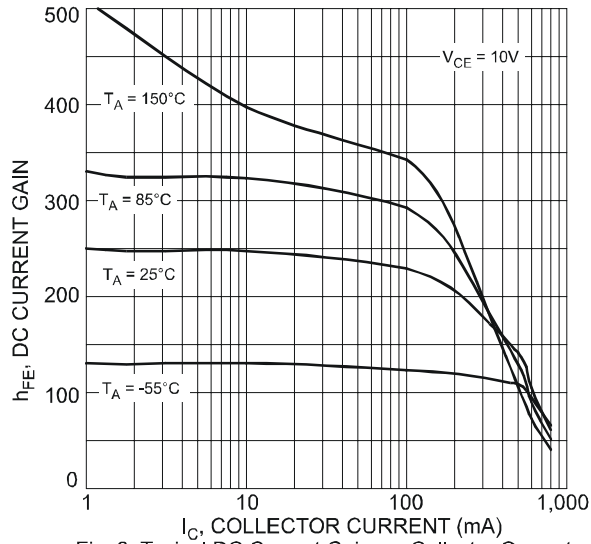


Fig. 3 Typical DC Current Gain vs. Collector Current

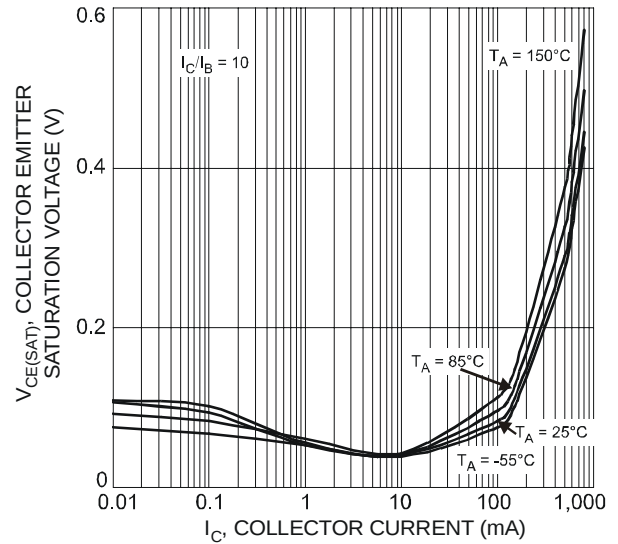


Fig. 4 Typical Collector Emitter Saturation Voltage vs. Collector Current

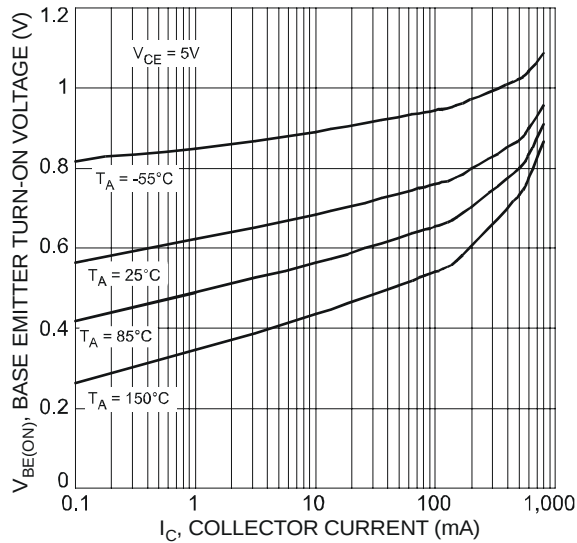


Fig. 5 Typical Base Emitter Turn-On Voltage vs. Collector Current

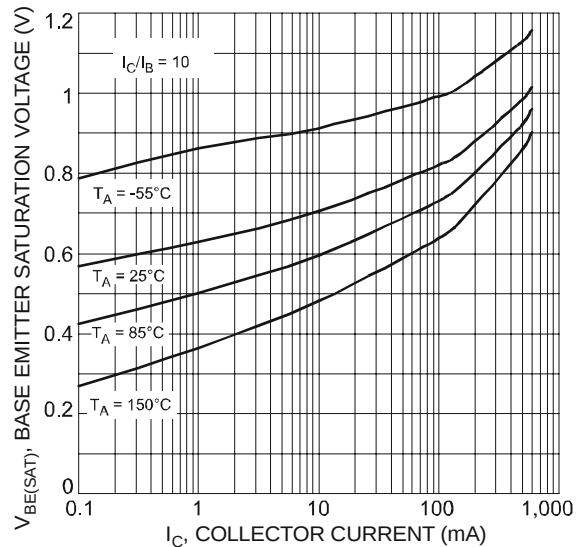


Fig. 6 Typical Base Emitter Saturation Voltage vs. Collector Current

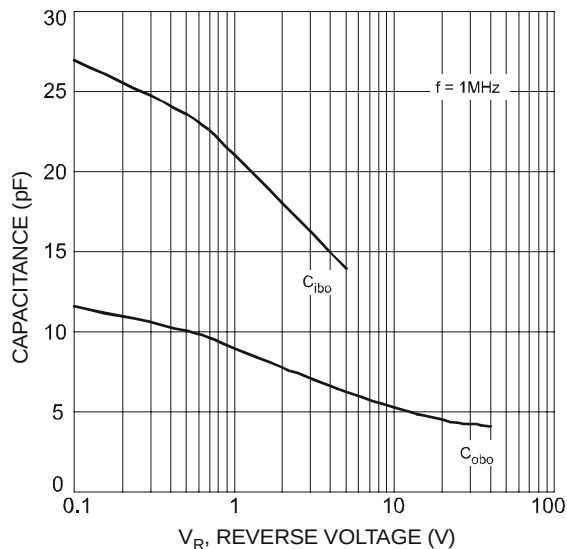


Fig. 7 Typical Capacitance Characteristics

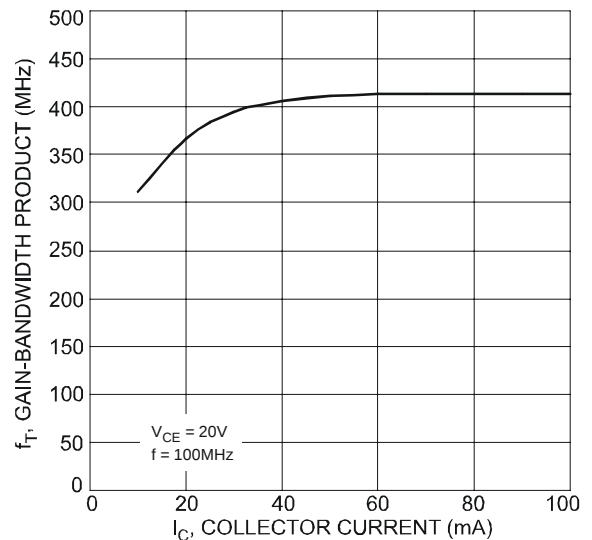


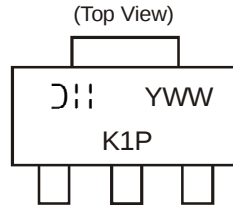
Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
DXT222A-13	SOT89-3L	2500/Tape & Reel

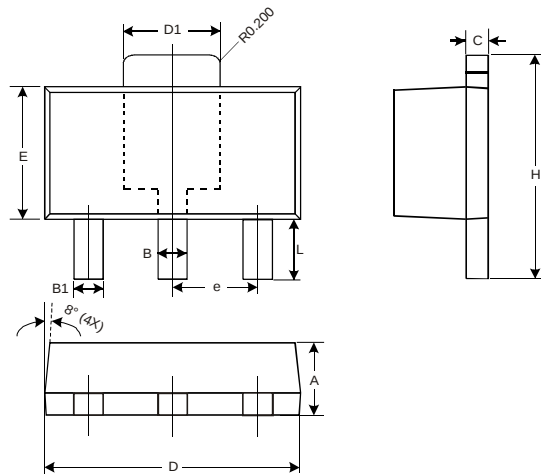
Notes: 5. For packaging details, go to our website at <http://www.diodes.com/ap02007.pdf>.

Marking Information



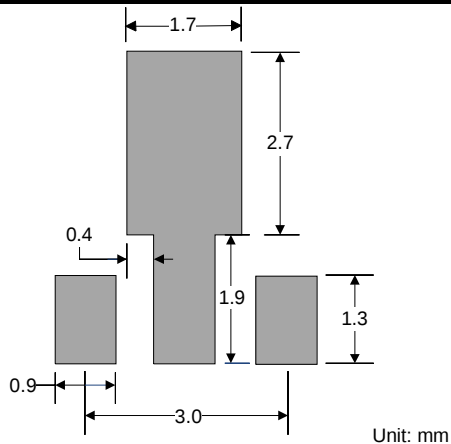
D11 = Manufacturer's code marking
 K1P = Product Type Marking Code
 YWW = Date Code Marking
 Y = Last digit of year ex: 7 = 2007
 WW = Week code 01 - 52

Package Outline Dimensions



SOT89-3L			
Dim	Min	Max	Typ
A	1.40	1.60	1.50
B	0.45	0.55	0.50
B1	0.37	0.47	0.42
C	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.50	1.70	1.60
E	2.40	2.60	2.50
e	—	—	1.50
H	3.95	4.25	4.10
L	0.90	1.20	1.05
All Dimensions in mm			

Suggested Pad Layout



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